	Application No.	Applicant(s)	
Notice of Allowability	10/045,895 Examiner	PARK, STEPHEN KEETAI Art Unit	
·			
	Hsien-Ming Lee	2823	
The MAILING DATE of this communication appeal All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI	(OR REMAINS) CLOSED in or other appropriate commit IGHTS. This application is s	n this application. If not included unication will be mailed in due course, THIS	
1. This communication is responsive to 10/2/03.			
2. The allowed claim(s) is/are 1-20,41 and 42.			
3. The drawings filed on 29 October 2001 are accepted by the Examiner.			
 4. ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) ☐ All b) ☐ Some* c) ☐ None of the: 			
Certified copies of the priority documents have been received.			
2. Certified copies of the priority documents have been received in Application No			
3. 🔲 Copies of the certified copies of the priority documents have been received in this national stage application from the			
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
5. Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application) since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.			
(a) The translation of the foreign language provisional application has been received.			
6. Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121 since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.			
Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application. THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.			
7. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.			
8. CORRECTED DRAWINGS (as "replacement sheets") must be submitted.			
(a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached			
1) 🗌 hereto or 2) 🔲 to Paper No			
(b) ☐ including changes required by the proposed drawing correction filed, which has been approved by the Examiner.			
(c) 🔲 including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No			
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t			
9. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FOR 1			
Attachment(s)			
1⊠ Notice of References Cited (PTO-892)	5☐ Notice of Inf	ormal Patent Application (PTO-152)	
2 Notice of Draftperson's Patent Drawing Review (PTO-948)		mmary (PTO-413), Paper No	
3 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No	^{8),} 7□ Examiner's ⁄	Amendment/Comment	
4 Examiner's Comment Regarding Requirement for Deposit	8⊠ Examiner's	Statement of Reasons for Allowance	
of Biological Material	9 Other		
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DETAILED ACTION

Remarks

1. The objection to claim 1 and double patenting rejection are withdrawn.

2. Claims 1-20, 41 and 42 are pending in the application.

Allowable Subject Matter

- 3. Claims 1-20, 41 and 42 are allowed.
- 4. The following is an examiner's statement of reasons for allowance:

The prior art of record, Boeck et al. to US 5880,018, teach a method of forming a copper interconnect, the method comprising:

- * forming a first sacrificial dielectric layer 18 above a structure layer 16/12 (Fig. 1);
- * forming an opening in the first sacrificial dielectric layer 18;
- * forming at least one barrier metal layer (Ta, col. 4, lines 20-28) above the first sacrificial dielectric layer 18 and in the opening;
- * depositing copper layer above the at least one barrier metal layer (Ta) in the opening;
- * forming the copper interconnect by removing the copper layer and the at least one barrier metal layer above the first sacrificial dielectric layer 18 by CMP technique, leaving the copper interconnect 20 in the opening (Fig. 3);
- * removing the first sacrificial dielectric layers 18 above the structure layer 16/12 and adjacent the copper interconnect 20 (Fig. 4); and
- * forming a low dielectric constant dielectric layer 22 by chemical vapor deposition above the structure layer 16/12 and adjacent the copper interconnect 20 (Fig. 5).

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Allowance."

In contrast, the cited prior art neither teaches nor suggests forming a second sacrificial dielectric layer above the first sacrificial dielectric layer; forming an opening in the second sacrificial dielectric layer; forming the copper interconnect by removing portions of the copper layer above the second sacrificial dielectric layer; forming the second sacrificial dielectric layer out of one of an oxide, an oxynitride, silicon dioxide, a nitrogen-bearing oxide, a nitrogen-doped oxide, silicon oxynitride, a high dielectric constant (high K) material, wherein K is at least about

5. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for

8; and forming a first sacrificial dielectric layer adjacent an intermetal via connect.

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hsien-Ming Lee whose telephone number is 703-305-7341. The examiner can normally be reached on M-F (9:00 \sim 5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone number for the organization where this application or proceeding is assigned is 703-308-7382.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

Hsien-Ming Lee Examiner Art Unit 2823

Bui Ming Lee

Dec. 21, 2003